

Hideo Hosono

List of Publications by Year in descending order

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Version: 2024-02-01

1,240
papers

88,712
citations

664

126
h-index

704

260
g-index

1325
all docs

1325
docs citations

1325
times ranked

39903
citing authors

#	ARTICLE	IF	CITATIONS
1	Electron Transfer from Support/Promotor to Metal Catalyst: Requirements for Effective Support. <i>Catalysis Letters</i> , 2022, 152, 307-314.	1.4	19
2	Suppression of Rayleigh Scattering in Silica Glass by Codoping Boron and Fluorine: Molecular Dynamics Simulations with Force-Matching and Neural Network Potentials. <i>Journal of Physical Chemistry C</i> , 2022, 126, 2264-2275.	1.5	11
3	Room-Temperature Fast H ⁺ Conduction in Oxygen-Substituted Lanthanum Hydride. <i>Journal of the American Chemical Society</i> , 2022, 144, 1523-1527.	6.6	27
4	LaRuSi Electride Disrupts the Scaling Relations for Ammonia Synthesis. <i>Chemistry of Materials</i> , 2022, 34, 1677-1685.	3.2	19
5	Fishtail effect and the vortex phase diagram of high-entropy alloy superconductor. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	7
6	Electronic and Lattice Thermal Conductivity Switching by 3D [→] 2D Crystal Structure Transition in Nonequilibrium (Pb _{1-x}) ₂ (Sn _x) ₂ Se. <i>Advanced Electronic Materials</i> , 2022, 8, .	2.6	6
7	Caging-Pnictogen-Induced Superconductivity in Skutterudites IrX ₃ (X = As, P). <i>Journal of the American Chemical Society</i> , 2022, 144, 6208-6214.	6.6	13
8	Degenerated Hole Doping and Ultra-Low Lattice Thermal Conductivity in Polycrystalline SnSe by Nonequilibrium Isovalent Te Substitution. <i>Advanced Science</i> , 2022, 9, e2105958.	5.6	7
9	Hexagonal BaTiO ₃ Hydroxide as a Water-Durable Catalyst Support for Chemoselective Hydrogenation. <i>Journal of the American Chemical Society</i> , 2022, 144, 6453-6464.	6.6	18
10	Characteristic mechanism for fast H ⁺ conduction in	3.8	8
11	High-Performance Channel Tin Halide Perovskite Thin Film Transistor Utilizing a 2D [→] 3D Core [→] Shell Structure. <i>Advanced Science</i> , 2022, 9, e2104993.	5.6	21
12	High-Mobility Metastable Rock-Salt Type (Sn,Ca)Se Thin Film Stabilized by Direct Epitaxial Growth on a YSZ (111) Single-Crystal Substrate. <i>ACS Applied Materials & Interfaces</i> , 2022, 14, 18682-18689.	4.0	1
13	Design, Synthesis, and Optoelectronic Properties of the High-Purity Phase in Layered A ₂ N ₂ (A = Sr, Ba; TM = Ti, Zr, Hf) Semiconductors. <i>Inorganic Chemistry</i> , 2022, 61, 6650-6659.	1.9	4
14	Characteristic Resistive Switching of Rare-Earth Oxyhydrides by Hydride Ion Insertion and Extraction. <i>ACS Applied Materials & Interfaces</i> , 2022, 14, 19766-19773.	4.0	3
15	Low Residual Carrier Density and High In-Grain Mobility in Polycrystalline Zn ₃ N ₂ Films on a Glass Substrate. <i>ACS Applied Electronic Materials</i> , 2022, 4, 2026-2031.	2.0	0
16	Pressure-induced reemergence of superconductivity in BaIr ₂ Ge ₇ and Ba ₃ Ir ₄ Ge ₁₆ with cage structures. <i>Matter and Radiation at Extremes</i> , 2022, 7, .	1.5	19
17	Unique Catalytic Mechanism for Ru-Loaded Ternary Intermetallic Electrides for Ammonia Synthesis. <i>Journal of the American Chemical Society</i> , 2022, 144, 8683-8692.	6.6	38
18	Ammonia Decomposition Mediated by Anion Vacancy at the Interface between CaNH with a Rock Salt Structure and Ni Nanoparticle. <i>Nihon Kessho Gakkaishi</i> , 2022, 64, 160-164.	0.0	0

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19	Catalyst for Ammonia Synthesis; History and Current Status. Journal of the Institute of Electrical Engineers of Japan, 2022, 142, 346-350.	0.0	0
20	Unconventional excitonic states with phonon sidebands in layered silicon diphosphide. Nature Materials, 2022, 21, 773-778.	13.3	20
21	Unique Conduction Band Minimum of Semiconductors Possessing a Zincblende-Type Framework. Inorganic Chemistry, 2022, 61, 10359-10364.	1.9	3
22	Hole Concentration Reduction in CuI by Zn Substitution and its Mechanism: Toward Device Applications. ACS Applied Materials & Interfaces, 2022, 14, 33463-33471.	4.0	9
23	18-Crown-6 Additive to Enhance Performance and Durability in Solution-Processed Halide Perovskite Electronics. Small, 2022, 18, .	5.2	4
24	How fluorine minimizes density fluctuations of silica glass: Molecular dynamics study with machine-learning assisted force-matching potential. Materials and Design, 2021, 197, 109210.	3.3	18
25	Double Charge Polarity Switching in Sb-Doped SnSe with Switchable Substitution Sites. Advanced Functional Materials, 2021, 31, 2008092.	7.8	7
26	Superconductivity from buckled-honeycomb-vacancy ordering. Science Bulletin, 2021, 66, 327-331.	4.3	1
27	Ruthenium Catalysts Promoted by Lanthanide Oxyhydrides with High Hydride-Ion Mobility for Low-Temperature Ammonia Synthesis. Advanced Energy Materials, 2021, 11, 2003723.	10.2	45
28	Ethanol-ethylene conversion mechanism on hydrogen boride sheets probed by <i>in situ</i> infrared absorption spectroscopy. Physical Chemistry Chemical Physics, 2021, 23, 7724-7734.	1.3	16
29	Ammonia Synthesis: Ruthenium Catalysts Promoted by Lanthanide Oxyhydrides with High Hydride-Ion Mobility for Low-Temperature Ammonia Synthesis (Adv. Energy Mater. 4/2021). Advanced Energy Materials, 2021, 11, 2170018.	10.2	1
30	Ship-in-a-Bottle Synthesis of High Concentration of N ₂ Molecules in a Cage-Structured Electride. Journal of Physical Chemistry Letters, 2021, 12, 1295-1299.	2.1	8
31	Why Ca ₂ NH works as an efficient and stable support of Ru catalyst in ammonia synthesis. Research on Chemical Intermediates, 2021, 47, 235-248.	1.3	1
32	Stabilization Factor of Anion-Excess Fluorite Phase for Fast Anion Conduction. Chemistry of Materials, 2021, 33, 1867-1874.	3.2	10
33	15.1: Invited Paper: Understanding and controlling electronic defects in amorphous oxide semiconductor. Digest of Technical Papers SID International Symposium, 2021, 52, 97-99.	0.1	0
34	Advances in Materials and Applications of Inorganic Electrides. Chemical Reviews, 2021, 121, 3121-3185.	23.0	125
35	Reversible 3D-2D structural phase transition and giant electronic modulation in nonequilibrium alloy semiconductor, lead-tin-selenide. Science Advances, 2021, 7, .	4.7	6
36	Molecular dynamics study on the co-doping effect of Al ₂ O ₃ and fluorine to reduce Rayleigh scattering of silica glass. Journal of the American Ceramic Society, 2021, 104, 5001-5015.	1.9	13

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37	Two-dimensional bipolar ferromagnetic semiconductors from layered antiferromagnets. <i>Physical Review Materials</i> , 2021, 5, .	0.9	22
38	MXene Phase with C ₃ Structure Unit: A Family of 2D Electrides. <i>Advanced Functional Materials</i> , 2021, 31, 2100009.	7.8	13
39	Crystal and electronic structure engineering of tin monoxide by external pressure. <i>Journal of Advanced Ceramics</i> , 2021, 10, 565-577.	8.9	11
40	High-Entropy van der Waals Materials Formed from Mixed Metal Dichalcogenides, Halides, and Phosphorus Trisulfides. <i>Journal of the American Chemical Society</i> , 2021, 143, 7042-7049.	6.6	55
41	Electronic and crystal structures of LnFeAsO _{1-x} H _x (Ln = La, Sm) studied by x-ray absorption spectroscopy, x-ray emission spectroscopy, and x-ray diffraction (part I): Tj ETQq1 1 0.784314 rgBT /Overlock 10 T	0.7	0
42	B ₅ N ₃ and B ₇ N ₅ Monolayers with High Carrier Mobility and Excellent Optical Performance. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 4823-4832.	2.1	18
43	Origins of the coloration from structure and valence state of bismuth oxide glasses. <i>Journal of Non-Crystalline Solids</i> , 2021, 560, 120720.	1.5	10
44	Electronic and crystal structures of LnFeAsO _{1-x} H _x (Ln = La, Sm) studied by x-ray absorption spectroscopy, x-ray emission spectroscopy, and x-ray diffraction: II pressure dependence. <i>Journal of Physics Condensed Matter</i> , 2021, 33, 255603.	0.7	0
45	2D Electrides: MXene Phase with C ₃ Structure Unit: A Family of 2D Electrides (Adv. Funct.) Tj ETQq1 1,0.784314 rgBT /O	7.8	13
46	Local Structure Properties of Hydrogenated and Nonhydrogenated Amorphous InGaZnO Thin Films Using XAFS and High-Energy XRD. <i>Journal of Physical Chemistry C</i> , 2021, 125, 13619-13628.	1.5	1
47	Electron-Deficient-Type Electride Ca ₅ Pb ₃ : Extension of Electride Chemical Space. <i>Journal of the American Chemical Society</i> , 2021, 143, 8821-8828.	6.6	22
48	High-Performance Indium Gallium Tin Oxide Transistors with an Al ₂ O ₃ Gate Insulator Deposited by Atomic Layer Deposition at a Low Temperature of 150 Å°C: Roles of Hydrogen and Excess Oxygen in the Al ₂ O ₃ Dielectric Film. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 28451-28461.	4.0	32
49	C ₂ Vacancy-Mediated N ₂ Activation over Ni-Loaded Rare-Earth Dicarbides for Ammonia Synthesis. <i>ACS Catalysis</i> , 2021, 11, 7595-7603.	5.5	5
50	Chemical stability of hydrogen boride nanosheets in water. <i>Communications Materials</i> , 2021, 2, .	2.9	15
51	A View on Formation Gap in Transition Metal Hydrides and Its Collapse. <i>Journal of the American Chemical Society</i> , 2021, 143, 11345-11348.	6.6	9
52	Floating Interlayer and Surface Electrons in 2D Materials: Graphite, Electrides, and Electrenes. <i>Small Science</i> , 2021, 1, 2100020.	5.8	10
53	Ion Substitution Effect on Defect Formation in Two-Dimensional Transition Metal Nitride Semiconductors, (i>AE</i>TiN ₂ (i>AE</i> = Ca, Sr, and Ba). <i>Inorganic Chemistry</i> , 2021, 60, 10227-10234.	1.9	3
54	Ammonia Decomposition over CaNH-Supported Ni Catalysts via an NH ² -Vacancy-Mediated Mars-van Krevelen Mechanism. <i>ACS Catalysis</i> , 2021, 11, 11005-11015.	5.5	45

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55	Dissociative and Associative Concerted Mechanism for Ammonia Synthesis over Co-Based Catalyst. <i>Journal of the American Chemical Society</i> , 2021, 143, 12857-12866.	6.6	50
56	Unintended Carbon-Related Impurity and Negative Bias Instability in High-Mobility Oxide TFTs. <i>IEEE Electron Device Letters</i> , 2021, 42, 1319-1322.	2.2	32
57	Comment on Weber et al. Mayenite-Based Electride $C_{12}A_7e^{\ominus}$: A Reactivity and Stability Study. <i>Catalysts</i> 2021, 11, 334. <i>Catalysts</i> , 2021, 11, 1154.	1.6	0
58	Ultrafast optical stress on $BaFe_2As_2$. <i>Physical Review Research</i> , 2021, 3, .	1.3	3
59	Origin of Metallic Nature of Na_3N . <i>Journal of the American Chemical Society</i> , 2021, 143, 69-72.	6.6	8
60	Crystalline boron monosulfide nanosheets with tunable bandgaps. <i>Journal of Materials Chemistry A</i> , 2021, 9, 24631-24640.	5.2	21
61	Breaking of Thermopower-Conductivity Trade-Off in $LaTiO_3$ Film around Mott Insulator to Metal Transition. <i>Advanced Science</i> , 2021, 8, 2102097.	5.6	6
62	Large phonon drag thermopower boosted by massive electrons and phonon leaking in $LaAlO_3/LaNiO_3/LaAlO_3$ heterostructure. <i>Nano Letters</i> , 2021, 21, 9240-9246.	4.5	6
63	Facile Synthesis of Ti_2AC (A = Zn, Al, In, and Ga) MAX Phases by Hydrogen Incorporation into Crystallographic Voids. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 11245-11251.	2.1	6
64	Mobility-stability trade-off in oxide thin-film transistors. <i>Nature Electronics</i> , 2021, 4, 800-807.	13.1	115
65	Superconductivity in the Layered Cage Compound $Ba_3Rh_4Ge_{16}$. <i>Chinese Physics Letters</i> , 2021, 38, 127402.	1.3	2
66	Electronic Correlation Strength of Inorganic Electrides from First Principles. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 12020-12025.	2.1	6
67	First-Principles and Microkinetic Study on the Mechanism for Ammonia Synthesis Using Ru-Loaded Hydride Catalyst. <i>Journal of Physical Chemistry C</i> , 2020, 124, 2070-2078.	1.5	25
68	Improved polaronic transport under a strong Mott-Hubbard interaction in Cu-substituted NiO. <i>Inorganic Chemistry Frontiers</i> , 2020, 7, 853-858.	3.0	6
69	Transition Metal-doped Ru Nanoparticles Loaded on Metal Hydrides for Efficient Ammonia Synthesis from First Principles. <i>Journal of Physical Chemistry C</i> , 2020, 124, 1529-1534.	1.5	3
70	Geometrical Frustration of B-H Bonds in Layered Hydrogen Borides Accessible by Soft Chemistry. <i>CheM</i> , 2020, 6, 406-418.	5.8	35
71	Strain Engineering at Heterointerfaces: Application to an Iron Pnictide Superconductor, Cobalt-Doped $BaFe_2As_2$. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 50096-50104.	4.0	5
72	Computational Prediction of Boron-Based MAX Phases and MXene Derivatives. <i>Chemistry of Materials</i> , 2020, 32, 6947-6957.	3.2	89

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73	Vacancy-enabled N ₂ activation for ammonia synthesis on an Ni-loaded catalyst. <i>Nature</i> , 2020, 583, 391-395.	13.7	309
74	Intermetallic ZrPd ₃ -Embedded Nanoporous ZrC as an Efficient and Stable Catalyst of the Suzuki Cross-Coupling Reaction. <i>ACS Catalysis</i> , 2020, 10, 14366-14374.	5.5	13
75	A Highly Efficient and Stable Blue-Emitting Cs ₅ Cu ₃ Cl ₆ I ₂ with a 1D Chain Structure. <i>Advanced Materials</i> , 2020, 32, e2002945.	11.1	73
76	Contribution of Nitrogen Vacancies to Ammonia Synthesis over Metal Nitride Catalysts. <i>Journal of the American Chemical Society</i> , 2020, 142, 14374-14383.	6.6	126
77	Magnetism induced by interlayer electrons in the quasi-two-dimensional electride $Y_{2}C$: Inelastic neutron scattering study. <i>Physical Review B</i> , 2020, 102, .	1.1	9
78	Boosting carrier mobility and stability in indium-zinc-tin oxide thin-film transistors through controlled crystallization. <i>Scientific Reports</i> , 2020, 10, 18868.	1.6	21
79	Potential Interaction of Noble Gas Atoms and Anionic Electrons in Ca ₂ N. <i>Journal of Physical Chemistry C</i> , 2020, 124, 12213-12219.	1.5	3
80	p-type Transparent Quadruple Perovskite Halide Conductors: Fact or Fiction?. <i>Advanced Functional Materials</i> , 2020, 30, 1909906.	7.8	17
81	Pressure-Induced Topological and Structural Phase Transitions in an Antiferromagnetic Topological Insulator*. <i>Chinese Physics Letters</i> , 2020, 37, 066401.	1.3	50
82	Heavily Hydride-ion-doped 1111-type Iron-based Superconductors: Synthesis, Physical Properties and Electronic Structure. <i>Journal of the Physical Society of Japan</i> , 2020, 89, 051006.	0.7	13
83	Ferromagnetic quasi-atomic electrons in two-dimensional electride. <i>Nature Communications</i> , 2020, 11, 1526.	5.8	57
84	Phonon scattering limited mobility in the representative cubic perovskite semiconductors SrGeO ₃ , BaSnO ₃ , and SrTiO ₃ . <i>Applied Physics Express</i> , 2020, 13, 073002.	1.1	5
85	Critical temperature and critical current density of hydrogen-doped SmFeAsO epitaxial films fabricated by thermal annealing with binary hydrides. <i>Applied Physics Express</i> , 2020, 13, 073002.	1.1	5
86	Air-Stable Calcium Cyanamide-Supported Ruthenium Catalyst for Ammonia Synthesis and Decomposition. <i>ACS Applied Energy Materials</i> , 2020, 3, 6573-6582.	2.5	27
87	Anomalous Charge State Evolution and Its Control of Superconductivity in M ₃ Al ₂ C (M = Mo, W). <i>IScience</i> , 2020, 23, 101196.	1.9	2
88	Hydrogen Boride Sheets as Reductants and the Formation of Nanocomposites with Metal Nanoparticles. <i>Chemistry Letters</i> , 2020, 49, 789-793.	0.7	16
89	Anisotropic structure of alkali metaphosphate glasses. <i>Journal of the American Ceramic Society</i> , 2020, 103, 3631-3641.	1.9	13
90	Stable single platinum atoms trapped in sub-nanometer cavities in 12CaO·7Al ₂ O ₃ for chemoselective hydrogenation of nitroarenes. <i>Nature Communications</i> , 2020, 11, 1020.	5.8	94

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91	Extraordinary Strong Band-Edge Absorption in Distorted Chalcogenide Perovskites. <i>Solar Rrl</i> , 2020, 4, 1900555.	3.1	82
92	Toward 2D Magnets in the $(\text{MnBi}_{2-x}\text{Te}_{4-x})(\text{Bi}_{2-x}\text{Te}_{3-x})_{1-x}$ Bulk Crystal. <i>Advanced Materials</i> , 2020, 32, e2001815.	11.1	45
93	Solid solution for catalytic ammonia synthesis from nitrogen and hydrogen gases at 50°C. <i>Nature Communications</i> , 2020, 11, 2001.	5.8	103
94	Shallow Valence Band of Rutile GeO_2 and P-type Doping. <i>Journal of Physical Chemistry C</i> , 2020, 124, 25721-25728.	1.5	18
95	Efficient Ammonia Synthesis over Phase-Separated Nickel-Based Intermetallic Catalysts. <i>Journal of Physical Chemistry C</i> , 2020, 124, 28589-28595.	1.5	15
96	Coexistence of magnetism and superconductivity in thin films of the Fe-based superconductor $\text{Ba}_{1-x}\text{La}_x\text{Fe}_2\text{As}_2$. <i>Journal of Physics Condensed Matter</i> , 2020, 32, 485804.	0.7	6
97	Higher-order topological crystalline insulating phase and quantized hinge charge in topological electrified apatite. <i>Physical Review Research</i> , 2020, 2, .	1.3	17
98	Growth, Properties, and Device Fabrication of Iron-Based Superconductor Thin-Films. , 2020, , 213-241.		0
99	Transition Metal-Doped Amorphous Oxide Semiconductor Thin-Film Phosphor, Chromium-Doped Amorphous Gallium Oxide. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800198.	0.8	6
100	On the Origin of the Negative Thermal Expansion Behavior of YCu. <i>Inorganic Chemistry</i> , 2019, 58, 11819-11827.	1.9	0
101	Hydrogenated Borophene Shows Catalytic Activity as Solid Acid. <i>ACS Omega</i> , 2019, 4, 14100-14104.	1.6	42
102	Structure and photoelastic constant of binary ns ² -type metal cation containing silicate glasses. <i>Journal of Non-Crystalline Solids</i> , 2019, 521, 119526.	1.5	9
103	Intrinsic and Extrinsic Defects in Layered Nitride Semiconductor SrTiN_2 . <i>Journal of Physical Chemistry C</i> , 2019, 123, 19307-19314.	1.5	9
104	Cation Clustering in Intermetallics: The Modular Bonding Schemes of CaCu and Ca ₂ Cu. <i>Inorganic Chemistry</i> , 2019, 58, 10313-10322.	1.9	4
105	Heteroepitaxial Thin-Film Growth of a Ternary Nitride Semiconductor CaZn_2N_2 . <i>ACS Applied Electronic Materials</i> , 2019, 1, 1433-1438.	2.0	16
106	Performance boosting strategy for perovskite light-emitting diodes. <i>Applied Physics Reviews</i> , 2019, 6, 031402.	5.5	88
107	Amorphous Oxide Semiconductor Thin-Film Transistors. , 2019, , 573-587.		3
108	Exotic Crystal Structures and Electronic Structures in Novel Structured Inorganic Materials. , 2019, , 107-120.		0

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109	Robust two-gap strong coupling superconductivity associated with low-lying phonon modes in pressurized Nb ₅ Ir ₃ O superconductors. Chinese Physics B, 2019, 28, 107401.	0.7	4
110	Symmetric Ambipolar Thin-Film Transistors and High-Gain CMOS-like Inverters Using Environmentally Friendly Copper Nitride. ACS Applied Materials & Interfaces, 2019, 11, 35132-35137.	4.0	12
111	Tunable Light Emission through the Range 1.8–3.2 eV and p-Type Conductivity at Room Temperature for Nitride Semiconductors, Ca(Mg _{1-x} Zn _x) ₂ N ₂ (0 ≤ x ≤ 1). J. Appl. Phys. 151, 074301 (2022)	1.9	15
112	New Amorphous InGaZnO Thin-Film Transistor-Based Optical Pixel Sensor for Optical Input Signal With Short Wavelength. IEEE Transactions on Electron Devices, 2019, 66, 3841-3846.	1.6	1
113	Crystal Structure Built from a GeO ₆ –GeO ₅ Polyhedra Network with High Thermal Stability: SrGe ₂ O ₅ . ACS Applied Electronic Materials, 2019, 1, 1989-1993.	2.0	5
114	Amorphous IGZO TFT with High Mobility of ~470 cm ² /V s via Vertical Dimension Control Using PEALD. ACS Applied Materials & Interfaces, 2019, 11, 40300-40309.	4.0	188
115	Insulator-like behavior coexisting with metallic electronic structure in strained FeSe thin films grown by molecular beam epitaxy. Physical Review B, 2019, 99, .	1.1	7
116	Quantum dynamics of hydrogen in the iron-based superconductor LaFeAsO _D measured with inelastic neutron spectroscopy. Physical Review B, 2019, 99, .		
117	Pressure-induced quantum critical point in the heavily hydrogen-doped iron-based superconductor LaFeAsO. Physical Review B, 2019, 99, .	1.1	4
118	News Poster: NBTS-free Oxide TFTs with High Mobility of 40 cm ² /Vs: A Possible Origin for NBTS Instability. Digest of Technical Papers SID International Symposium, 2019, 50, 1349-1350.	0.1	2
119	Hydrogen-Insertion-Induced Itinerant Ferromagnetism in Zr ₂ CoH _{4.8} with Co Chains. Journal of Physical Chemistry C, 2019, 123, 14964-14968.	1.5	2
120	Characteristic fast H ⁺ ion conduction in oxygen-substituted lanthanum hydride. Nature Communications, 2019, 10, 2578.	5.8	70
121	Discovery of hexagonal ternary phase Ti ₂ InB ₂ and its evolution to layered boride TiB. Nature Communications, 2019, 10, 2284.	5.8	159
122	Acid-durable electride with layered ruthenium for ammonia synthesis: boosting the activity via selective etching. Chemical Science, 2019, 10, 5712-5718.	3.7	42
123	Shubnikov–de Haas oscillations in the three-dimensional Dirac fermion system Ca ₃ PbO. Physical Review B, 2019, 99, .	1.1	4
124	Structure and Electronic Properties of [Ca ₂₄ Al ₂₈ O ₆₄] ⁴⁺ ·4e ⁻ Surfaces: Opportunities for Termination-Controlled Electron Transfer. Journal of Physical Chemistry C, 2019, 123, 6030-6036.	1.5	8
125	Material Design of Green-Light-Emitting Semiconductors: Perovskite-Type Sulfide SrHfS ₃ . Journal of the American Chemical Society, 2019, 141, 5343-5349.	6.6	59
126	Large magnetocaloric effect in van der Waals crystal CrBr ₃ . Frontiers of Physics, 2019, 14, 1.	2.4	20

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127	Particulate Generation on Surface of Iron Selenide Films by Air Exposure. <i>Journal of Superconductivity and Novel Magnetism</i> , 2019, 32, 3047-3055.	0.8	3
128	Stabilization and heteroepitaxial growth of metastable tetragonal FeS thin films by pulsed laser deposition. <i>Superconductor Science and Technology</i> , 2019, 32, 054002.	1.8	5
129	Low anisotropic upper critical fields in SmO _{1-x} F _x /FeAs thin films with a layered hybrid structure. <i>Superconductor Science and Technology</i> , 2019, 32, 044003.	1.8	11
130	Pseudogap Control of Physical and Chemical Properties in CeFeSi-Type Intermetallics. <i>Inorganic Chemistry</i> , 2019, 58, 2848-2855.	1.9	4
131	Ternary inorganic electrides with mixed bonding. <i>Physical Review B</i> , 2019, 99, .	1.1	26
132	Electronic Defects in Amorphous Oxide Semiconductors: A Review. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800372.	0.8	179
133	Zeolitic Intermetallics: LnNiSi (Ln = La–Nd). <i>Journal of the American Chemical Society</i> , 2019, 141, 3376-3379.	6.6	27
134	Natural van der Waals heterostructural single crystals with both magnetic and topological properties. <i>Science Advances</i> , 2019, 5, eaax9989.	4.7	193
135	Low-Temperature Synthesis of Perovskite Oxynitride-Hydrides as Ammonia Synthesis Catalysts. <i>Journal of the American Chemical Society</i> , 2019, 141, 20344-20353.	6.6	106
136	Palladium-bearing intermetallic electride as an efficient and stable catalyst for Suzuki cross-coupling reactions. <i>Nature Communications</i> , 2019, 10, 5653.	5.8	43
137	One-step solution synthesis of white-light-emitting films via dimensionality control of the Cs–Cu–I system. <i>APL Materials</i> , 2019, 7, .	2.2	73
138	Ultra-wide bandgap amorphous oxide semiconductors for NBIS-free thin-film transistors. <i>APL Materials</i> , 2019, 7, .	2.2	69
139	Intermetallic Electride Catalyst as a Platform for Ammonia Synthesis. <i>Angewandte Chemie - International Edition</i> , 2019, 58, 825-829.	7.2	104
140	Direct Activation of Cobalt Catalyst by $12\text{CaO}\cdot 7\text{Al}_2\text{O}_3$ Electride for Ammonia Synthesis. <i>ACS Catalysis</i> , 2019, 9, 1670-1679.	5.5	68
141	Superconducting transition temperatures in the electronic and magnetic phase diagrams of $\text{Sr}_2\text{VF}_6\text{O}_3$, a superconductor. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 115801.	0.7	7
142	Multiple Color Inorganic Thin-Film Phosphor, RE-Doped Amorphous Gallium Oxide (RE = Rare Earth: Pr, Tj). <i>Journal of Applied Physics</i> , 2019, 125, 174101.	0.8	15
143	Effects of Base Pressure on Growth and Optoelectronic Properties of Amorphous InGaZnO: Ultralow Optimum Oxygen Supply and Bandgap Widening. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1700832.	0.8	14
144	Superconductivity at 48 K of heavily hydrogen-doped SmFeAsO epitaxial films grown by topotactic chemical reaction using Ca_2H_2 . <i>Physical Review Materials</i> , 2019, 3, .	0.9	19

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145	High Electron Density on Ru in Intermetallic YRu ₂ : The Application to Catalyst for Ammonia Synthesis. <i>Journal of Physical Chemistry C</i> , 2018, 122, 10468-10475.	1.5	43
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